

Amendments to the Specification:

Please replace the paragraph beginning at page 5, line 14, with the following amended paragraph:

In the insulating film consisting essentially of silicon oxide, thus formed by the above-mentioned method, halogen elements (e.g., fluorine or chlorine) are detected in an amount of from 1×10^{17} [[from]] to $5 \times 10^{20} \text{ cm}^{-3}$ as impurity elements by secondary ion mass spectrometry, while the carbon concentration is $5 \times 10^{19} \text{ cm}^{-3}$ or less. In particular, in order to lower the interfacial level density of the film, it is desired that the carbon concentration is $1 \times 10^{18} \text{ cm}^{-3}$ or less. In order to lower the carbon concentration, the temperature of the substrate during filming may be 200°C or higher, preferably 300°C or higher.

Please replace the paragraph beginning at page 11, line 9, with the following amended paragraph:

On the basis of the results obtained from the above-mentioned experiments, a TFT sample was produced. The flow sheet for producing it is shown in Fig. 2. First, the silicon oxide film 202 of 2000 Å thick was formed, as a ~~subbing~~ rubbing film, on the substrate (Corning 7059) 201, by positive column plasma CVD using TEOS, oxygen and TCE as raw materials. The apparatus used herein was the same as that shown in Fig. 1. The main conditions for the filming were as follows: